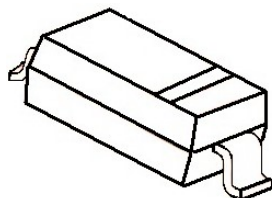


**1N5819WS****SOD-323 Plastic-Encapsulate Schottky Barrier Diode****SOD-323****Marking: S4****特征 Features**

- 大电流承受能力。High Current Capability
- 正向压降低。Low Forward Voltage Drop

机械数据 Mechanical Data

- 封装: SOD-323 封装 SOD-323 Small Outline Plastic Package
- 极性: 色环端为负极 Polarity: Color band denotes cathode end
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25℃ 除非另有规定)**Maximum Ratings & Thermal Characteristics** (Ratings at 25℃ ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	1N5819WS	单位 Unit
最大可重复峰值反向电压 Maximum repetitive peak reverse voltage	VRRM	40	V
最大均方根电压 Maximum RMS voltage	VRMS	28	V
最大直流阻断电压 Maximum DC blocking voltage	VDC	40	V
最大正向平均整流电流 Maximum average forward rectified current	IFM	350	mA
峰值正向浪涌电流 8.3ms 单一正弦半波 Peak forward surge current 8.3 ms single half sine-wave	IFSM	1.5	A
功率消耗 Power Dissipation	PD	200	mW
典型热阻 T ypical thermal resistance	RθJA	500	℃/W
工作结温 Operating junction temperature	Tj	125	℃
存储温度 Storage temperature range	TSTG	-50-+150	℃

电特性 (TA = 25℃ 除非另有规定)**Electrical Characteristics** (Ratings at 25℃ ambient temperature unless otherwise specified).

参数 Parameters	符号 Symbol	测试条件 Test conditions	1N5819WS	单位 Unit
最大正向电压 Maximum forward voltage	VF	IF = 20mA IF = 200mA	0.370 0.600	V
最大反向电压 Maximum reverse breakdown voltage	VR	IR=100uA	40	V
最大反向电流 Maximum reverse current	IR	VR=30V	5.0	uA
典型结电容 Type junction capacitance	Cj	VR =0V, f = 1MHz	50	pF
反向恢复时间 Reverse recovery time	Trr	IF=IR=200mA, Irr=0.1xIR,RL=100 Ω	10	ns

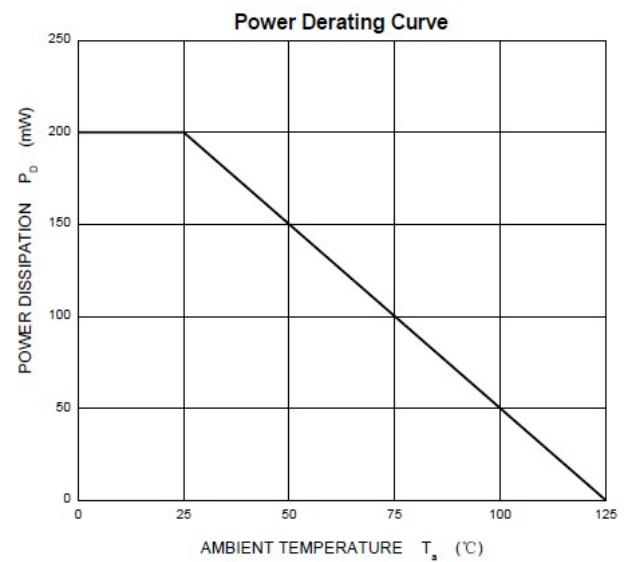
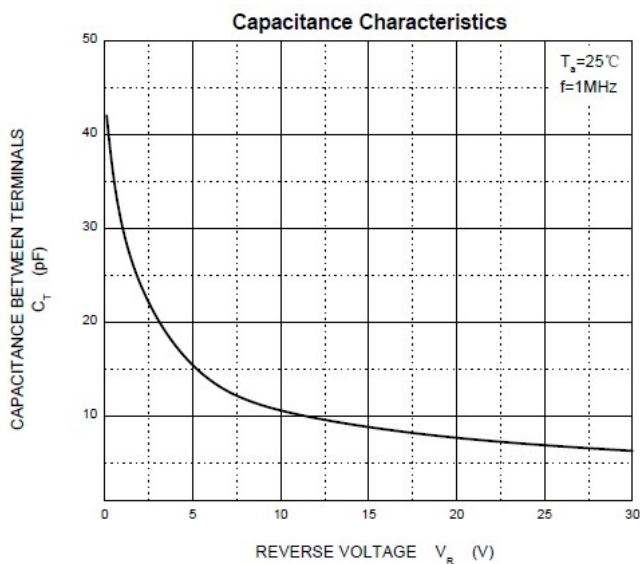
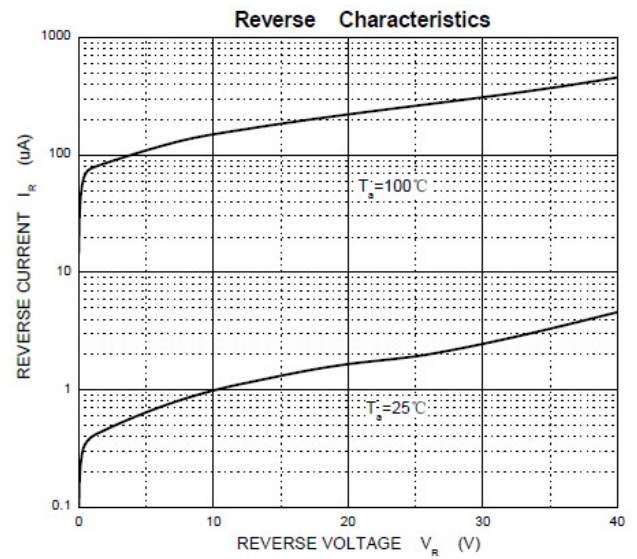
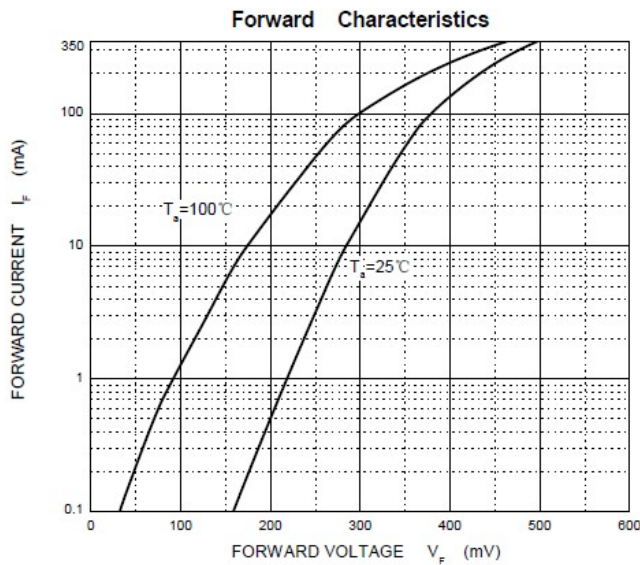




1N5819WS

SOD-323 Plastic-Encapsulate Schottky Barrier Diode

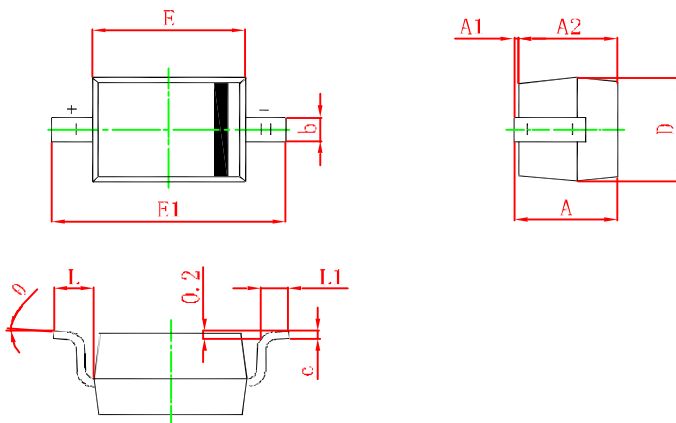
特性曲线 Characteristic Curves



SOD-323 PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



Symbol	Min.(mm)	Max.(mm)
A		1.000
A1	0.000	0.100
A2	0.800	0.900
b	0.250	0.350
c	0.080	0.150
D	1.200	1.400
E	1.600	1.800
E1	2.500	2.700
L	0.475REF	
L1	0.250	0.400
θ	0°	8°

